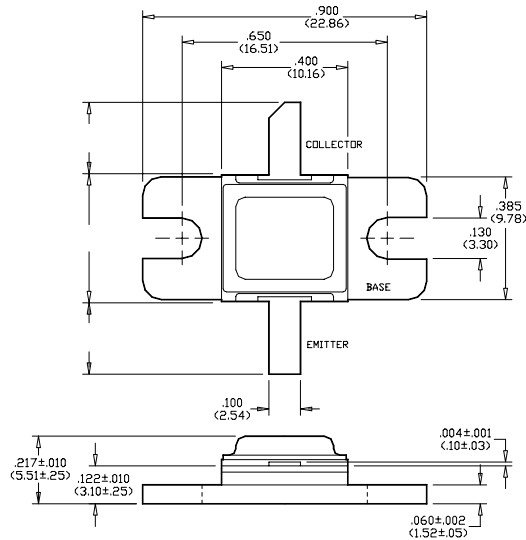


**FEATURES**

- Designed for Pulsed Avionics Applications
- NPN Silicon Microwave Power Transistor
- Common Base Configuration
- Broadband Class C Operation
- Diffused Emitter Ballasting Resistors
- Gold Metalization System
- Internal Input and Output Impedance Matching
- Hermetic Metal/Ceramic Package

**OUTLINE DRAWING**



**ABSOLUTE MAXIMUM RATINGS AT 25°C**

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	$V_{CES}$	70	V
Emitter-Base Voltage	$V_{EBO}$	3.0	V
Collector Current (Peak)	$I_C$	6	A
Total Power Dissipation	$P_D$	160	W
Storage Temperature	$T_{STG}$	-65 to +200	°C
Junction Temperature	$T_J$	200	°C

**ELECTRICAL CHARACTERISTICS AT 25°C**

Parameter	Symbol	Min	Max	Units	Test Conditions
Collector-Emitter Breakdown Voltage	$BV_{CES}$	70	-	V	$I_C=35mA$
Collector-Emitter Leakage Current	$I_{CES}$	-	3.5	mA	$V_{CE}=40V$
Thermal Resistance	$R_{TH(JC)}$	-	1.5	°C/W	$V_{CC}=45V, P_{out}=75W, F=1.03, 1.09GHz$
Output Power	$P_{OUT}$	75	-	W	$V_{CC}=45V, P_{in}=9W, F=1.03, 1.09GHz$
Power Gain	$G_P$	9	-	dB	$V_{CC}=45V, P_{out}=75W, F=1.03, 1.09GHz$
Collector Efficiency	$\eta_C$	45	-	%	$V_{CC}=45V, P_{out}=75W, F=1.03, 1.09GHz$
Input Return Loss	RL	8	-	dB	$V_{CC}=45V, P_{out}=75W, F=1.03, 1.09GHz$
Load Mismatch Tolerance	VSWR-T	-	3:1	-	$V_{CC}=45V, P_{out}=75W, F=1.03, 1.09GHz$
Load Mismatch Stability	VSWR-S	-	1.5:1	-	$V_{CC}=45V, P_{out}=75W, F=1.03, 1.09GHz$

**BROADBAND TEST FIXTURE IMPEDANCE**

F (MHz)	$Z_{IF} (\Omega)$	$Z_{OF} (\Omega)$
1030	2.6 - j6	9.4 + j2
1090	2.3 - j5.6	11 + j0.2

